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Form 1449 (Modified)  Information Disclosure Statement By Applicant  (Use Several Sheets if Necessary)	Atty Docket No. NOVLP090/NVLS-2888	Application No.: 10/733,858
	Applicant: Zhu et al.	
	Filing Date December 10, 2003	Group 2891

## U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub- class	Filing Date
<i>BKS</i>	A1	6,200,412	03.2001	Kilgore et al.			
	A2	6,232,196	5/12/01	Raaijmakers et al.			
	A3	2003/0207580	11/6/03	Li et al.			
	A4	5,384,068	11/10/98	Chern et al.			
	A5	2004/0082181	4/29/04	Doan et al.			
	A6	6,596,653	7/22/03	Tan et al.			
	A7	5,711,998	1/27/98	Shufflebotham			
	A8	6,184,158	2/6/01	Shufflebotham et al.			
	A9	2001/0044203	11.2001	Huang et al.			
	A10	5,129,958	07.1992	Nagashima et al.			
	A11	6,106,678	08.2000	Shufflebotham et al.			
	A12	2002/0179570	12.2002	Mathad et al.			
	A13	6,599,829	07.2003	Smith et al.			
	A14	5,252,178	10.1993	Moslehi, Mehrdad M.			
	A15	6,400,023	06.2002	Huang, Richard J.			
	A16	6,846,745 B1	01.25.05	Papasouliotis et al.			
	A17	6,136,703	10.2000	Vaartstra, Brian A.			
	A18	2002/0052119	05.2002	Van Cleemput			
	A19	6,794,290 B1	09.21.04	Papasouliotis et al.			
	A20	6,846,391 B1	01.25.05	Papasouliotis et al.			
	A21	6,410,446	06.2002	Tsai et al.			
	A22	6,737,334	05.2004	Ho et al.			
	A23	6,787,483 B1	09.07.04	Bayman et al.			
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	A25	6,124,211	09.2000	Butterbaugh et al.			
	A26	5,516,729	05.1996	Dawson et al.			
	A27	2004/0241342	12.2004	Karim et al.			
	A28	6,077,574	06.2000	Usami			
	A29	6,808,748 B2	10.2004	Kapoor et al.			
	A30	2004/0020894	02.2004	Williams et al.			
	A31	2003/0003244	01.2003	Rossman			
	A32	2003/0003682	01.2003	Moll et al.			
	A33	2003/0165632	09.2003	Lin et al.			
Examiner <i>BKS</i>	Date Considered 3/29/06						

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## Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation	
							Yes	No
	B1	JP 2003-031,649	01.2003	Japan				

## Other Documents

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BKS	C1	U.S. Office Action mailed August 6, 2003, from U.S. Application No. 10/058,897. [Atty Dkt. NOVLP040X1/NVLS-000607]
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	C6	U.S. Office Action mailed June 29, 2005, from U.S. Application No. 10/728,569. [Atty Dkt. NOVLP087/NVLS-2880]
	C7	Papasouliotis et al., "Hydrogen-Based Phosphosilicate Glass Process for Gap Fill of High Aspect Ratio Structures", Novellus Systems, Inc., filed October 11, 2002, Application No. 10/271,333, pages 1-28. [Atty Dkt No. NOVLP054/NVLS-000719].
	C8	Guari et al., "Method of Preventing Structures Erosion During Multi-Step Gap Fill", Novellus Systems, Inc., filed December 4, 2003, Application No. 10/728,569, pages 1-29. [Atty Dkt No. NOVLP087/NVLS-2880].
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	C12	Bayman et al., "Gap Fill For High Aspect Ratio Structures", Novellus Systems, Inc., filed July 13, 2004, Application No. 10/890,655, pages 1-24. [Atty Dkt No. NOVLP040D2/NVLS-000592D2].
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✓	C14	U.S. Office Action mailed November 17, 2005, from U.S. Application No. 10/316,987. [Atty Dkt. NOVLP053/NVLS-000706]
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## Other Documents

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JS/KS	C15	U.S. Office Action mailed April 30, 2004, from U.S. Application No. 10/389,164. [Atty Dkt. NOVLP061/NVLS-000756]
	C16	Sutanto et al., "Method For Controlling Etch Process Repeatability", Novellus Systems, Inc., filed September 2, 2003, Application No. 10/654,113, pages 1-31. [Atty Dkt No. NOVLP079/NVLS-002850].
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